

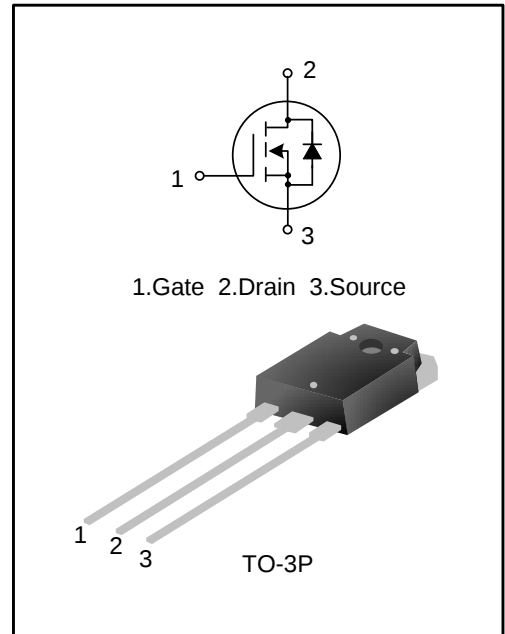
23A 500V N-CHANNEL MOSFET

GENERAL DESCRIPTION

SVF23N50PN is an N-channel enhancement mode power MOS field effect transistor which is produced using Silan proprietary F-Cell™ structure VDMOS technology. The improved planar stripe cell and the improved guard ring terminal have been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are widely used in AC-DC power suppliers, DC-DC converters and H-bridge PWM motor drivers.

FEATURES

- 23A, 500V, $R_{DS(on)(typ)}=0.21\Omega@V_{GS}=10V$
- Low gate charge
- Low C_{rss}
- Fast switching
- Improved dv/dt capability



ORDERING INFORMATION

Part No.	Package	Marking	Hazardous Substance Control	Packing Type
SVF23N50PN	TO-3P	23N50	Pb free	Tube

ABSOLUTE MAXIMUM RATINGS (T_C=25°C UNLESS OTHERWISE NOTED)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		V _{DS}	500	V
Gate-Source Voltage		V _{GS}	±30	V
Drain Current	T _C =25°C	I _D	23.0	A
	T _C =100°C		14.55	
Drain Current Pulsed		I _{DM}	92.0	A
Power Dissipation(T _C =25°C) -Derate above 25°C		P _D	280	W
			2.24	W/°C
Single Pulsed Avalanche Energy (Note 1)		E _{AS}	2044	mJ
Operation Junction Temperature Range		T _J	-55~+150	°C
Storage Temperature Range		T _{stg}	-55~+150	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Case	R _{θJC}	0.45	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	50	°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C UNLESS OTHERWISE NOTED)

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Drain -Source Breakdown Voltage	B _{VDS}	V _{GS} =0V, I _D =250μA	500	--	--	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =500V, V _{GS} =0V	--	--	1.0	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V	--	--	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D =250μA	2.0	--	4.0	V
Static Drain- Source On State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =11.5A	--	0.21	0.27	Ω
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	--	2595.8	--	pF
Output Capacitance	C _{oss}		--	343.8	--	
Reverse Transfer Capacitance	C _{rss}		--	10.1	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} =250V, R _G =10Ω, I _D =23.0A (note 2, 3)	--	42.2	--	ns
Turn-on Rise Time	t _r		--	79.0	--	
Turn-off Delay Time	t _{d(off)}		--	125.7	--	
Turn-off Fall Time	t _f		--	71.2	--	
Total Gate Charge	Q _g	V _{DD} =400V, V _{GS} =10V, I _D =23.0A (note 2, 3)	--	42.51	--	nC
Gate-Source Charge	Q _{gs}		--	12.9	--	
Gate-Drain Charge	Q _{gd}		--	14.34	--	

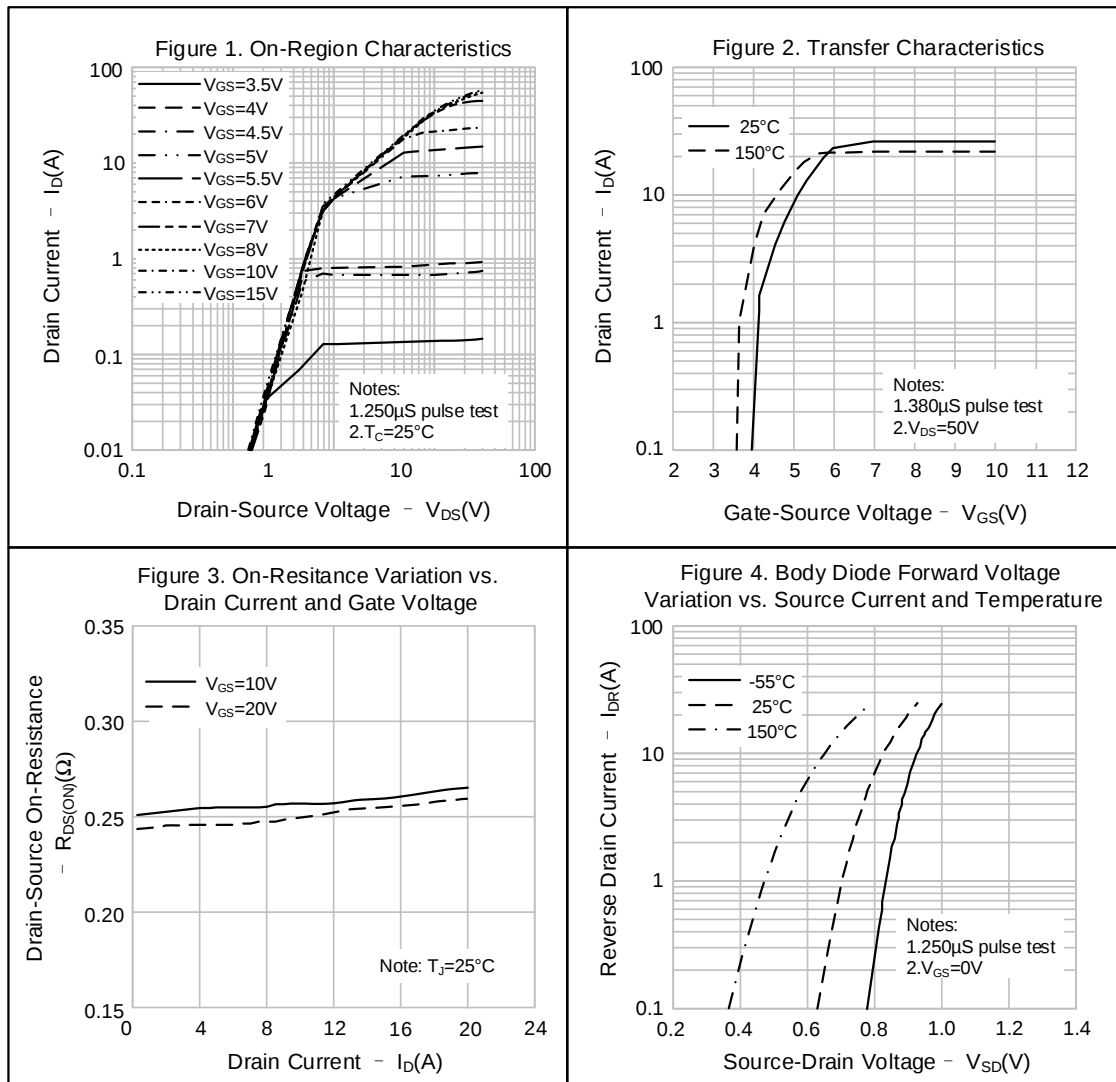
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	I_S	Integral Reverse P-N Junction Diode in the MOSFET	--	--	23.0	A
Pulsed Source Current	I_{SM}		--	--	92.0	
Diode Forward Voltage	V_{SD}	$I_S=23.0A, V_{GS}=0V$	--	--	1.4	V
Reverse Recovery Time	T_{rr}	$I_S=23.0A, V_{GS}=0V,$ $di_F/dt=100A/\mu s$ (Note 2)	--	578.21	--	ns
Reverse Recovery Charge	Q_{rr}		--	7.89	--	μC

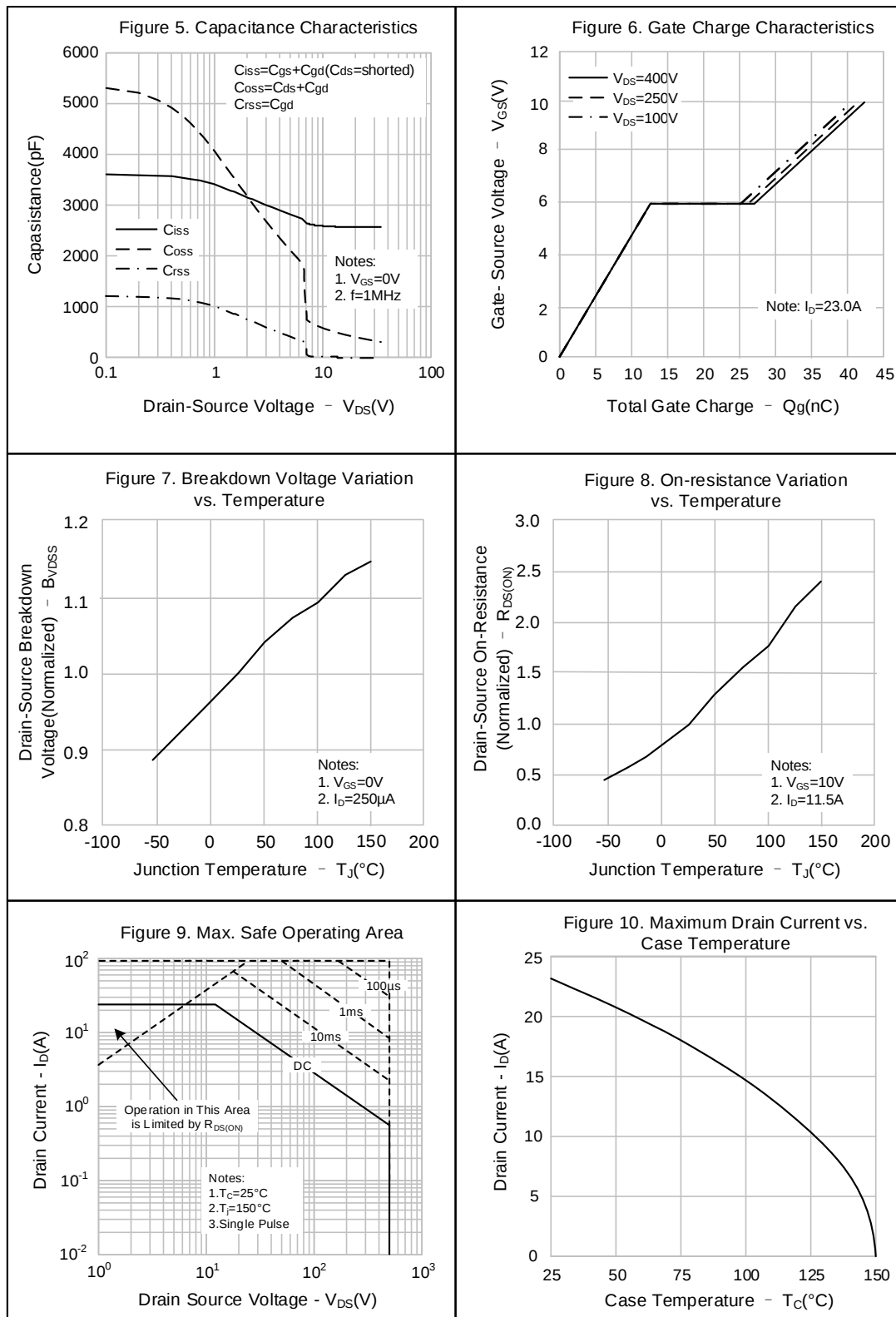
Notes:

1. $L=30mH, I_{AS}=10.65A, V_{DD}=100V, R_G=25\Omega$, starting $T_J=25^\circ C$;
2. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;
3. Essentially independent of operating temperature.

TYPICAL CHARACTERISTICS

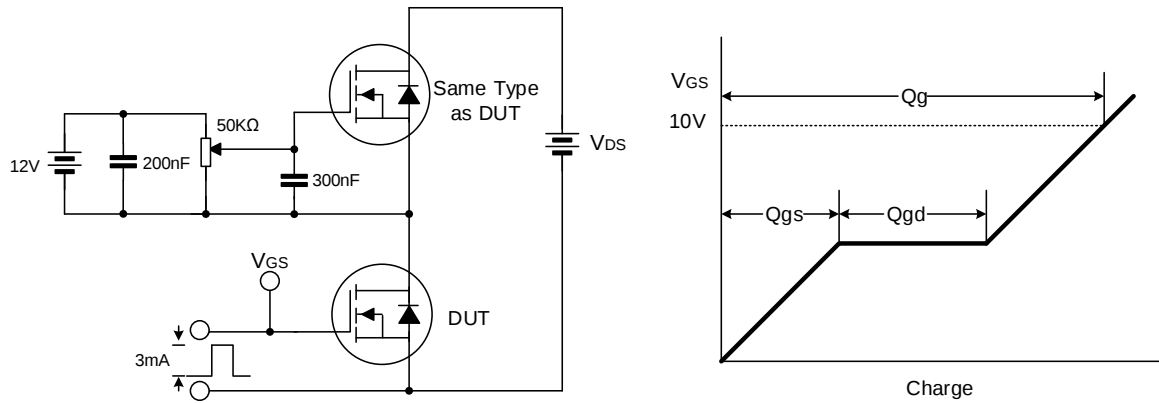


TYPICAL CHARACTERISTICS(CONTINUED)

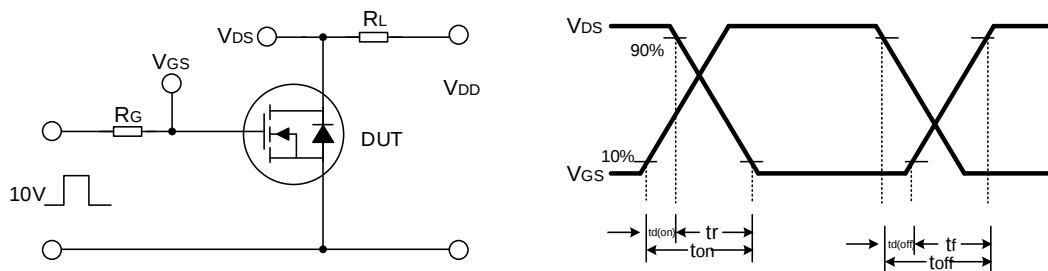


TYPICAL TEST CIRCUIT

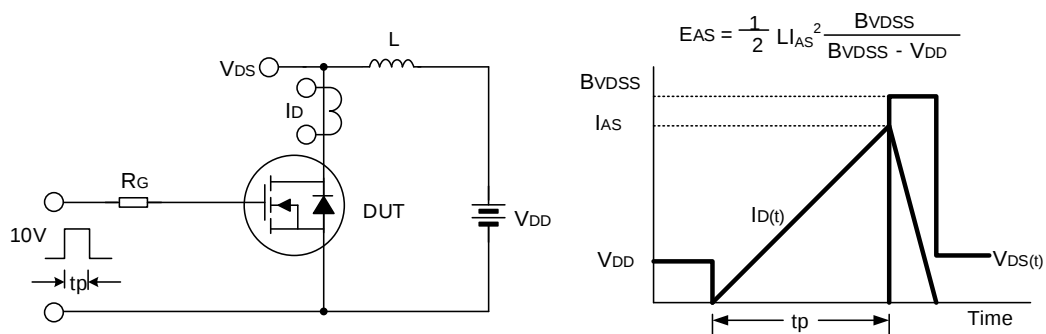
Gate Charge Test Circuit & Waveform



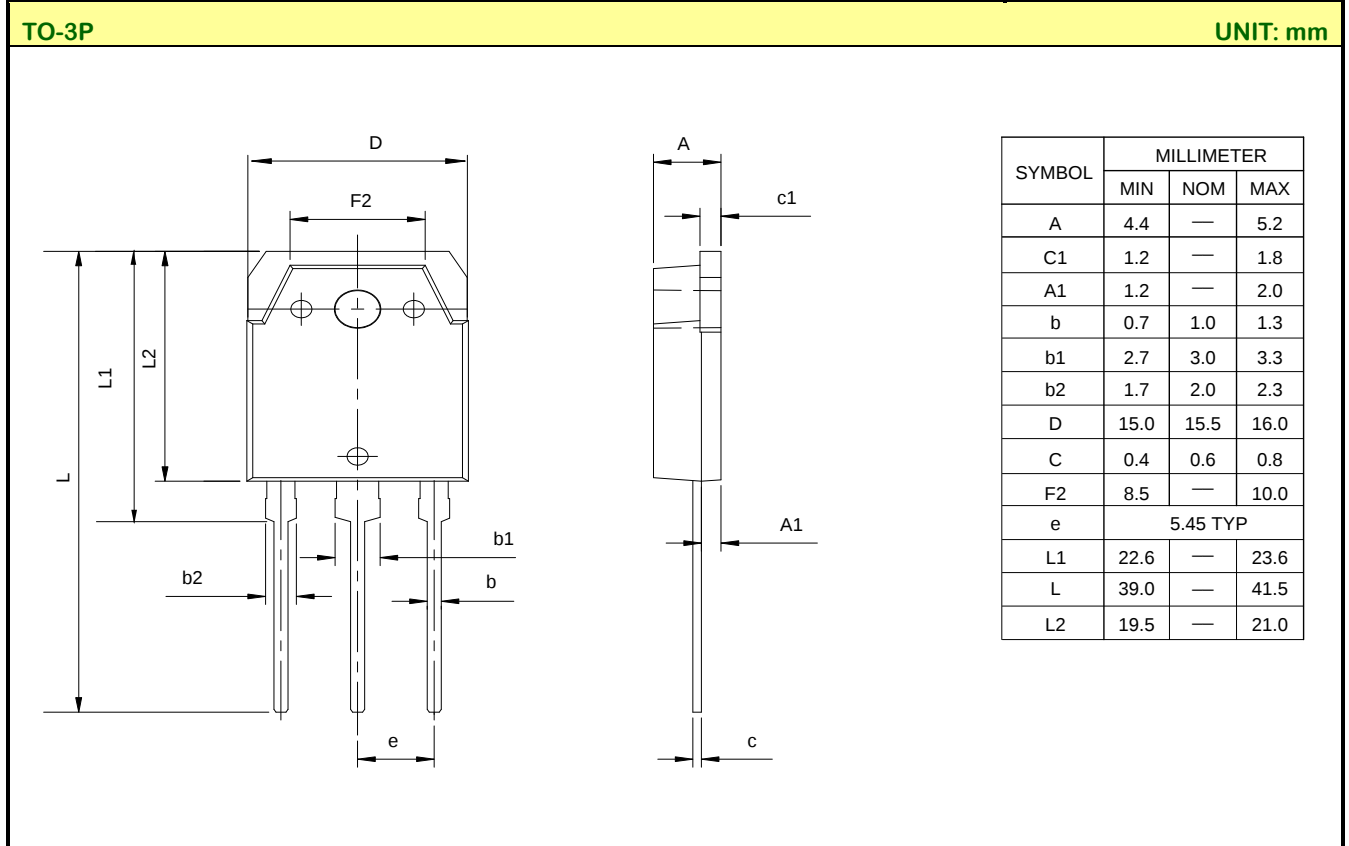
Resistive Switching Test Circuit & Waveform



Unclamped Inductive Switching Test Circuit & Waveform



PACKAGE OUTLINE



Important notice :

- The instructions are subject to change without notice! Customers should obtain the latest relevant information before placing orders and should verify that such information is complete and current.
- Our products are consumer electronic products, and / or civil electronic products.
- When using our products, please do not exceed the maximum rating of the products, otherwise the reliability of the whole machine will be affected. There is a certain possibility of failure or malfunction of any semiconductor product under specific conditions. The buyer is responsible for complying with safety standards and taking safety measures when using our products for system design, sample and whole machine manufacturing, so as to avoid potential failure risk that may cause personal injury or property loss.
- It is strongly recommended to identify the trademark when buying our products. Please contact us if there is any question.
- When exporting, using and reselling our products, buyer must comply with the international export control laws and regulations of China, the United States, the United Kingdom, the European Union and other countries & regions.
- Product promotion is endless, our company will wholeheartedly provide customers with better products!
- Website: <http://www.silan.com.cn>

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Rev.: 1.2

Revision History:

1. Deleted NOMENCLATURE
 2. Modify Important notice
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Rev.: 1.1

Revision History:

1. Modify ordering information
 2. Modify Part No.
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Rev.: 1.0

Revision History:

1. First release
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